

EAST - [10649906.wsp:1]

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 L1: (21) (magnetic adj random adj access adj memory or 'MRAM') and (magnetic near tunnel near jun...
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(magnetic adj random adj
 access adj memory or 'MRAM')
 and (magnetic near tunnel near
 junction or 'MTJ') and
 (tunneling near
 magneto-resistive or 'TMR')
 and (convex\$3 concav\$3
 warp\$3)

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20040052131 A1	20040318	13	Information storage device and manufacturing method thereof	365/202		
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20040004889 A1	20040108	219	Magnetic random access memory	365/222		
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20030210591 A1	20031113	35	Magnetic memory device and magnetic substrate	365/200		
12	<input type="checkbox"/>	<input type="checkbox"/>	US 20020145902 A1	20021010	83	Magnetic memory device and magnetic substrate	365/97		
13	<input type="checkbox"/>	<input type="checkbox"/>	US 20020130339 A1	20020919	39	Magnetoresistance effect device, method of manufacturing the same, magnetic	257/295	257/E21.665; 257/E27.005	
14	<input type="checkbox"/>	<input type="checkbox"/>	US 20020014667 A1	20020207	32	Method of horizontally growing carbon nanotubes and field effect transistor using	257/368	257/E51.004; 257/E51.005;	
15	<input type="checkbox"/>	<input type="checkbox"/>	US 6841820 B2	20050111	12	Information storage apparatus and manufacturing method therefor	257/295	257/298; 257/301;	
16	<input type="checkbox"/>	<input type="checkbox"/>	US 6803260 B2	20041012	32	Method of horizontally growing carbon nanotubes and field effect transistor using	438/142	257/E51.004; 257/E51.005;	
17	<input type="checkbox"/>	<input type="checkbox"/>	US 6794696 B2	20040921	19	Magnetic memory device and method of manufacturing the same	257/295	257/421; 257/424;	
18	<input type="checkbox"/>	<input type="checkbox"/>	US 6741495 B2	20040525	77	Magnetic memory device and magnetic substrate	365/158	365/171; 365/173	
19	<input type="checkbox"/>	<input type="checkbox"/>	US 6605836 B2	20030812	38	Magnetoresistance effect device, magnetic memory apparatus, personal digital	257/295	257/E21.665; 257/E27.005;	